Is Now Part of

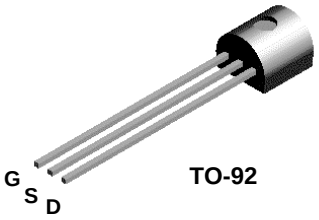
ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

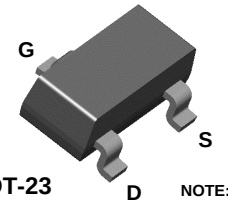
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD
SEMICONDUCTOR TM

2N5457 MMBF5457
2N5458 MMBF5458
2N5459 MMBF5459



TO-92



SOT-23
Mark: 6D / 61S / 6L

NOTE: Source & Drain are interchangeable

N-Channel General Purpose Amplifier

This device is a low level audio amplifier and switching transistors, and can be used for analog switching applications. Sourced from Process 55.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	- 25	V
I_{GF}	Forward Gate Current	10	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5457-5459	*MMBF5457-5459	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

N-Channel General Purpose Amplifier
(continued)

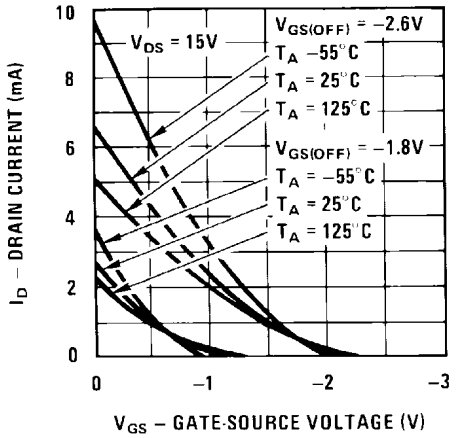
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 10 μA, V_{DS} = 0		- 25			V
I_{GSS}	Gate Reverse Current	V_{GS} = -15 V, V_{DS} = 0				- 1.0	nA
		V_{GS} = -15 V, V_{DS} = 0, T_A = 100°C				- 200	nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 15 V, I_D = 10 nA	**5457**	- 0.5		- 6.0	V
			5458	- 1.0		- 7.0	V
			5459	- 2.0		- 8.0	V
V_{GS}	Gate-Source Voltage	V_{DS} = 15 V, I_D = 100 μA	**5457**		- 2.5		V
		V_{DS} = 15 V, I_D = 200 μA	**5458**		- 3.5		V
		V_{DS} = 15 V, I_D = 400 μA	**5459**		- 4.5		V
ON CHARACTERISTICS							
I_{DSS}	Zero-Gate Voltage Drain Current*	V_{DS} = 15 V, V_{GS} = 0	**5457**	1.0	3.0	5.0	mA
			5458	2.0	6.0	9.0	mA
			5459	4.0	9.0	16	mA
SMALL SIGNAL CHARACTERISTICS							
g_{fs}	Forward Transfer Conductance*	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz					
			5457	1000		5000	μmhos
			5458	1500		5500	μmhos
			5459	2000		6000	μmhos
g_{os}	Output Conductance*	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz			10	50	μmhos
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz			4.5	7.0	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz			1.5	3.0	pF
NF	Noise Figure	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz, R_G = 1.0 megohm, BW = 1.0 Hz				3.0	dB

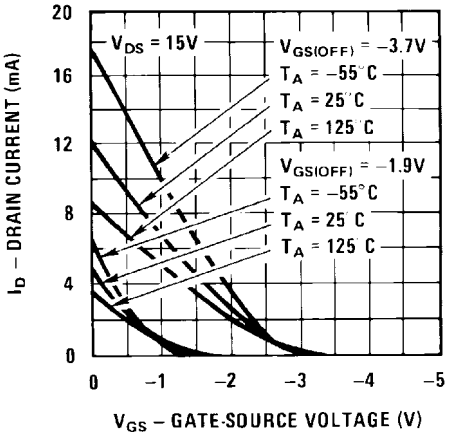
*Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2%

Typical Characteristics

Transfer Characteristics

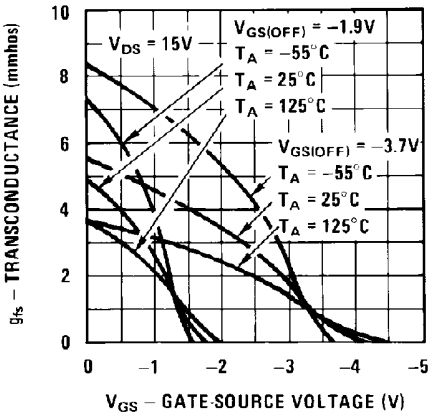


Transfer Characteristics

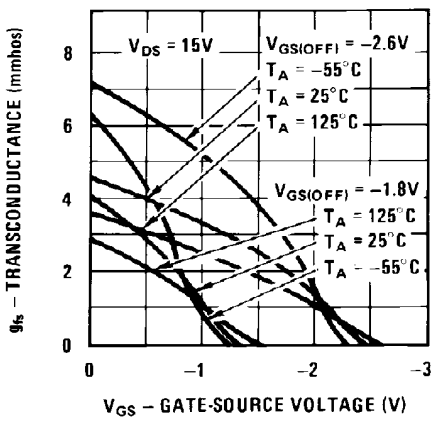


Typical Characteristics (continued)

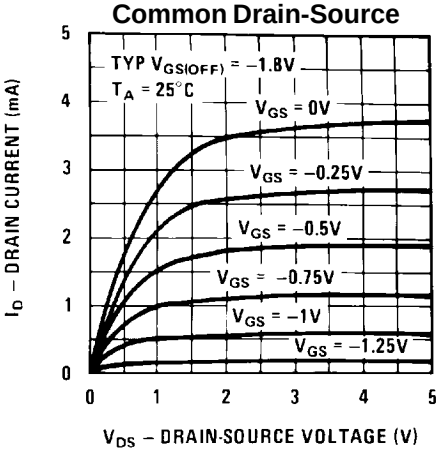
Transfer Characteristics



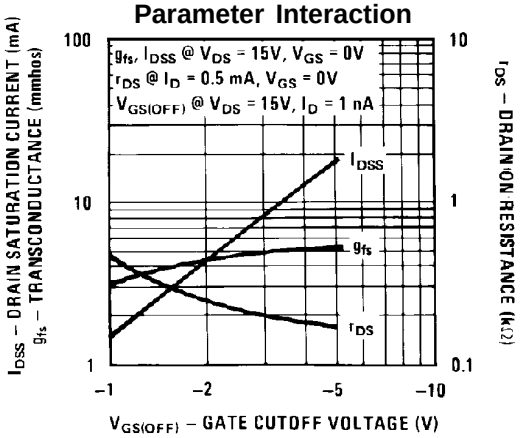
Transfer Characteristics



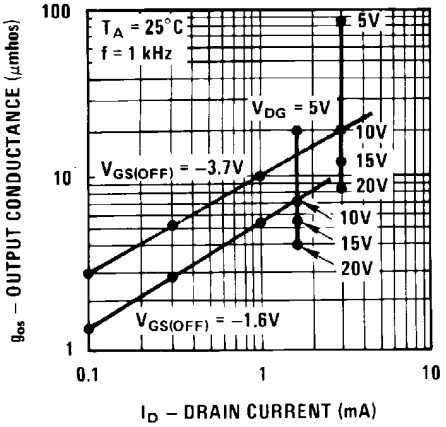
Common Drain-Source



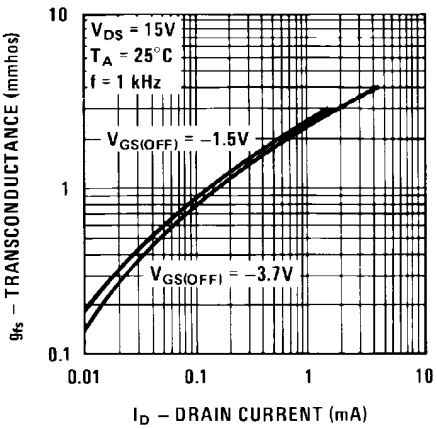
Parameter Interaction



Output Conductance vs. Drain Current

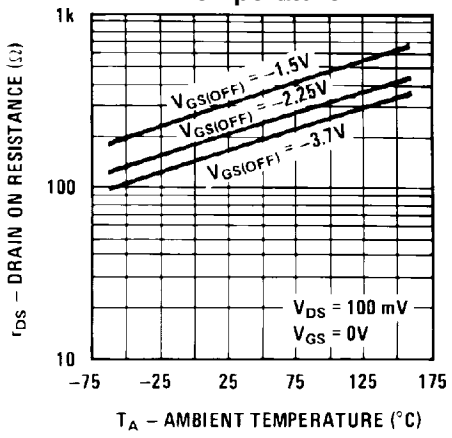


Transconductance vs. Drain Current

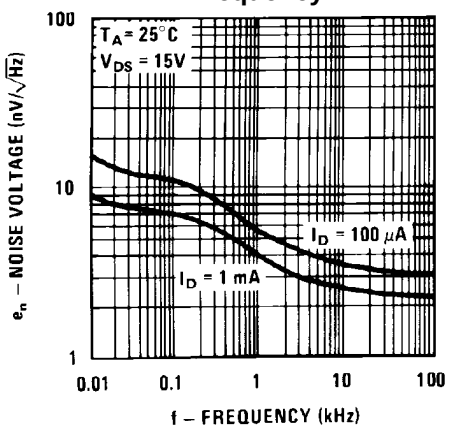


Typical Characteristics (continued)

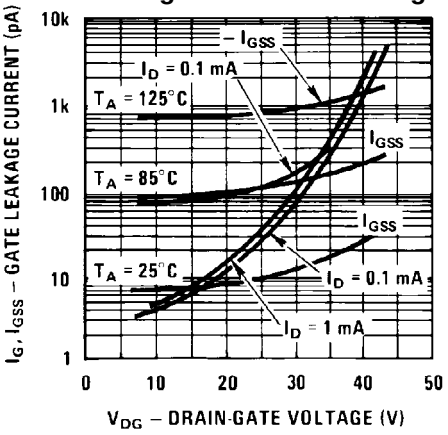
Channel Resistance vs. Temperature



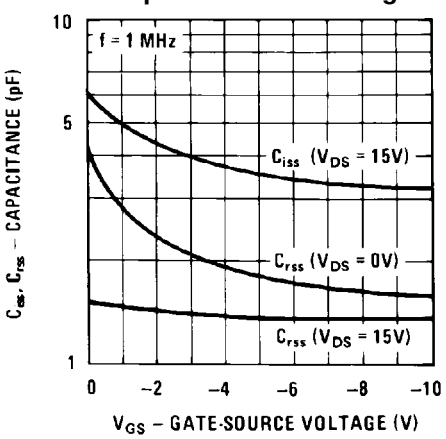
Noise Voltage vs. Frequency



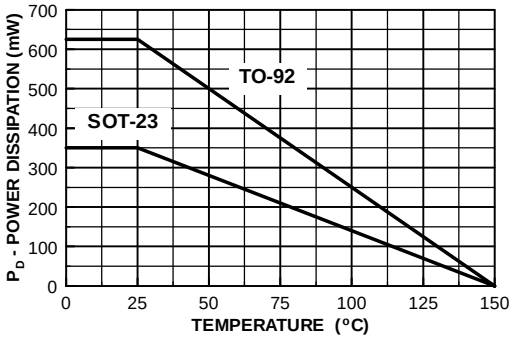
Leakage Current vs. Voltage



Capacitance vs. Voltage



Power Dissipation vs Ambient Temperature



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™
Bottomless™
CoolFET™
CROSSVOLT™
DOME™
E^2CMOS^{TM}
EnSigna™
FACT™
FACT Quiet Series™
FAST®
FASTr™
GlobalOptoisolator™
GTO™
HiSeC™
ISOPLANAR™
MICROWIRE™
OPTOLOGIC™
OPTOPLANAR™
PACMAN™
POP™
PowerTrench®
QFET™
QS™
QT Optoelectronics™
Quiet Series™
SILENT SWITCHER®
SMART START™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SyncFET™
TinyLogic™
UHC™
VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.
As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

2N5457_D26Z 2N5457_D27Z 2N5457_D74Z 2N5457_D75Z 2N5457_Q 2N5457_D74Z_Q